DMP3097L

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_A = +25°C
-30V	65mΩ @ V_{GS} = -10V	-3.9A
	99mΩ @ V_{GS} = -4.5V	-3.2A

Features and Benefits

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen- and Antimony-Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

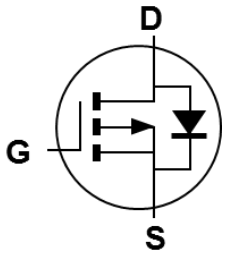
- Backlighting
- Power Management Functions
- DC-DC Converters

Mechanical Data

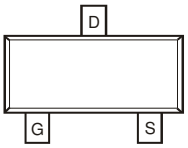
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

SOT23

Top View



Equivalent Circuit



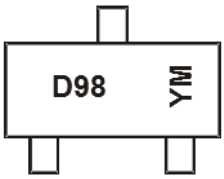
Top View
Pin Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3097L-7	SOT23	3000/Tape & Reel
DMP3097L-13	SOT23	10000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



D98= Product Type Marking Code
YM = Date Code Marking
$\overline{Y}$ = Year (ex: H = 2020)
M = Month (ex: 9 = September)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	H	I	J	K	L	M	N	O	P	R	S	T

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Drain Current (Note 6) V_{GS} = -10V	Steady State	T_A = +25°C T_A = +70°C	I_D	-3.9 -3.1	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-20	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	1.0	W
Thermal Resistance, Junction to Ambient @ T_A = +25°C (Note 5)	$R_{\theta JA}$	123	°C/W
Total Power Dissipation (Note 6)	P_D	1.52	W
Thermal Resistance, Junction to Ambient @ T_A = +25°C (Note 6)	$R_{\theta JA}$	82	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-800	nA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1.0	—	-2.1	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	53 74	65 99	mΩ	V_{GS} = -10V, I_D = -3.8A V_{GS} = -4.5V, I_D = -3.0A
Diode Forward Voltage (Note 6)	V_{SD}	—	-0.85	-1.26	V	V_{GS} = 0V, I_S = -2.7A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	563	—	pF	V_{DS} = -25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	48	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	41	—	pF	
Gate Resistance	R_G	—	9.5	—	Ω	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	6.6	—	nC	V_{DS} = -15V, V_{GS} = -4.5V, I_D = -3.8A
		—	13.4	—		V_{DS} = -15V, V_{GS} = -10V, I_D = -3.8A
Gate-Source Charge	Q_{gs}	—	2.5	—		
Gate-Drain Charge	Q_{gd}	—	1.5	—		
Turn-On Delay Time	$t_{D(ON)}$	—	10	—	ns	V_{DS} = -15V, V_{GS} = -10V, I_D = -1A, R_G = 6.0Ω
Turn-On Rise Time	t_R	—	2.3	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	31	—		
Turn-Off Fall Time	t_F	—	11	—		

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

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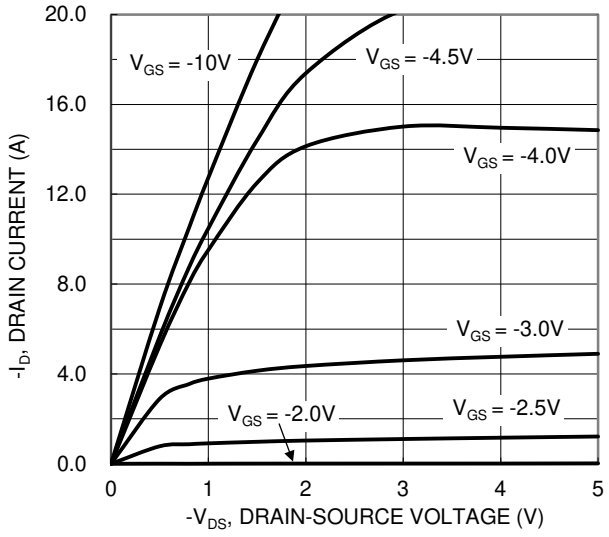

Figure 1.Typical Output Characteristic

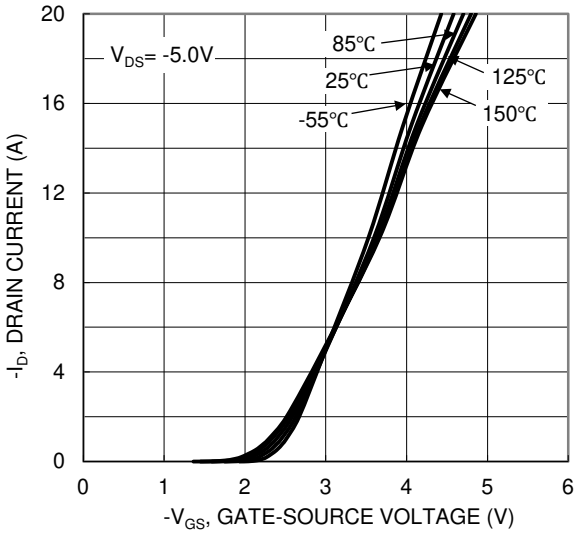

Figure 2. Typical Transfer Characteristic

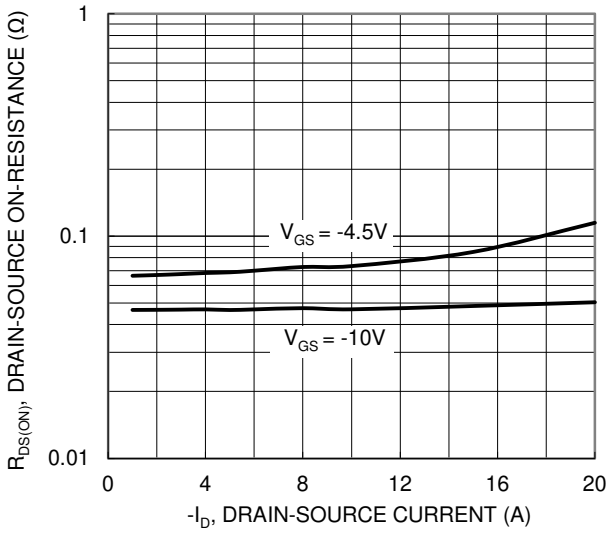

Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

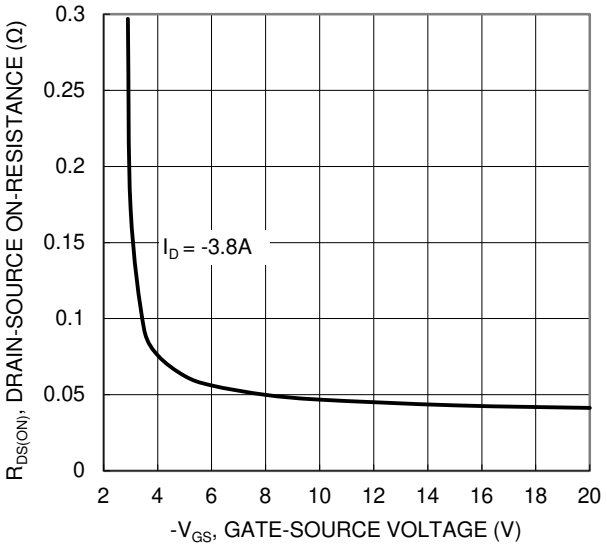

Figure 4. Typical Transfer Characteristic

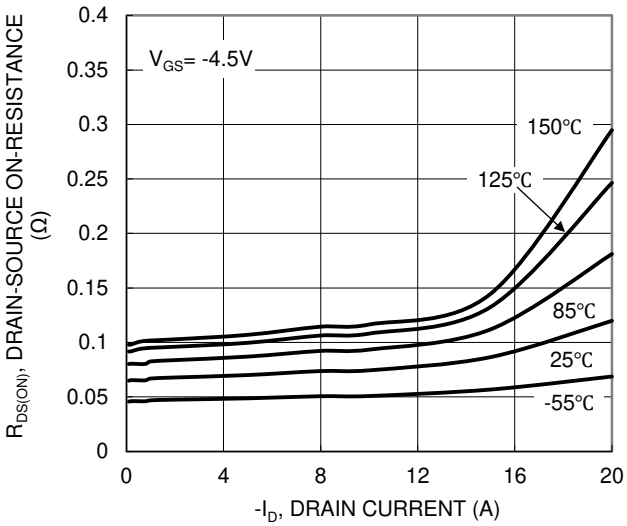

Figure 5. Typical On-Resistance vs. Drain Current and Temperature

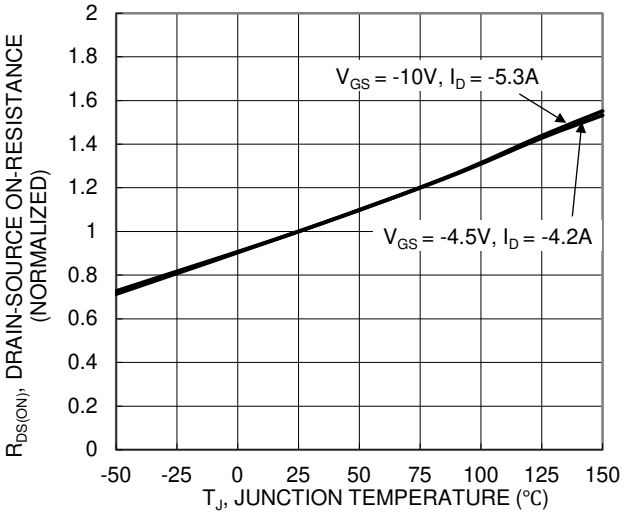

Figure 6. On-Resistance Variation with Temperature

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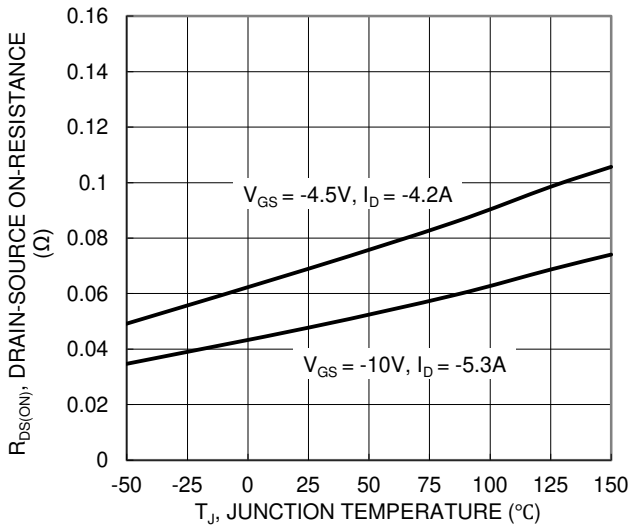

Figure 7. On-Resistance Variation with Temperature

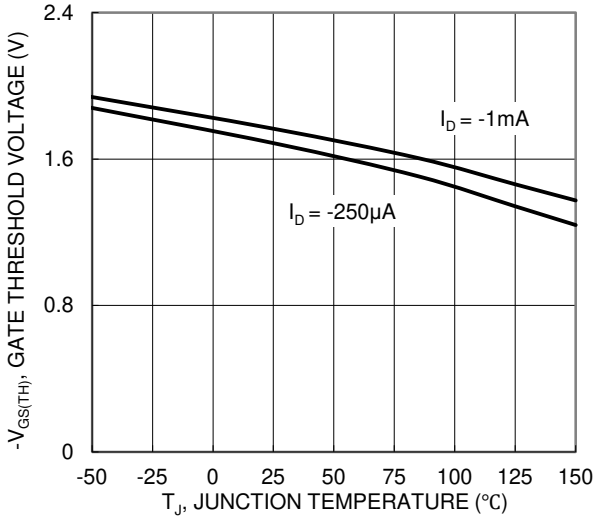

Figure 8. Gate Threshold Variation vs. JunctionTemperature

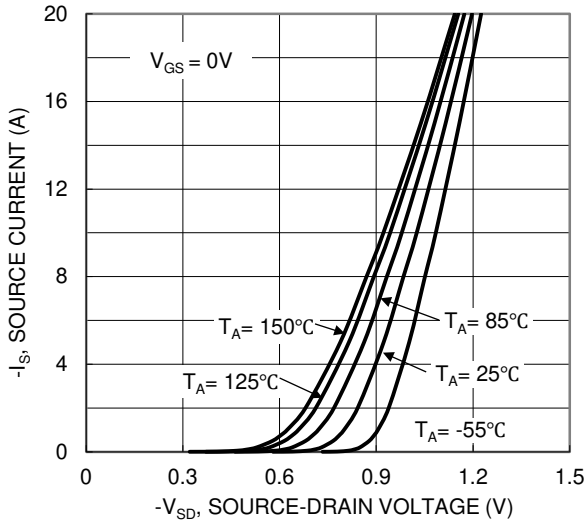

Figure 9. Diode Forward Voltage vs. Current

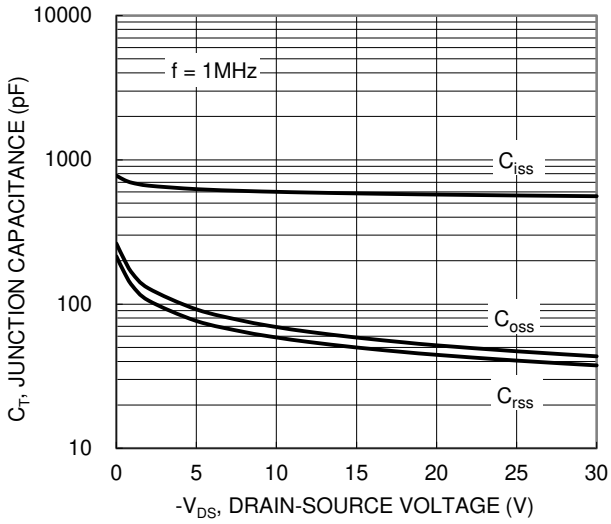

Figure 10. Typical Junction Capacitance

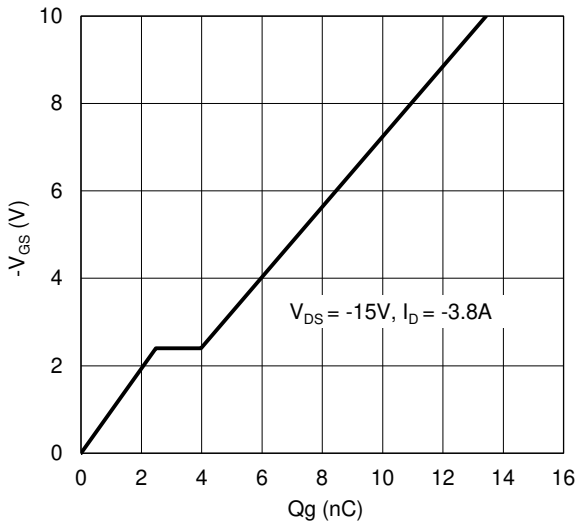

Figure 11. Gate Charge

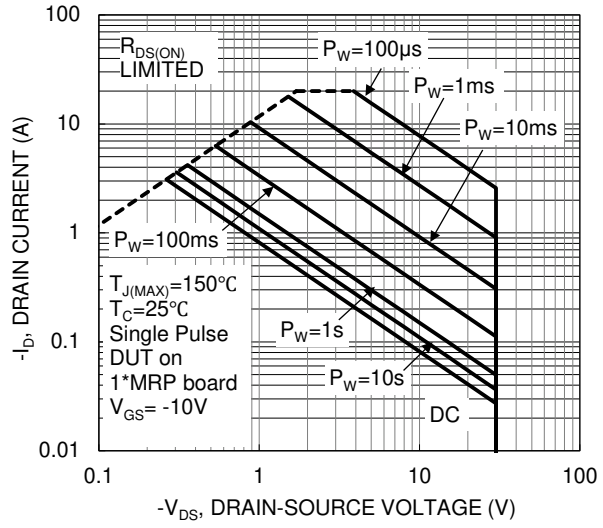

Figure 12. SOA, Safe Operation Area

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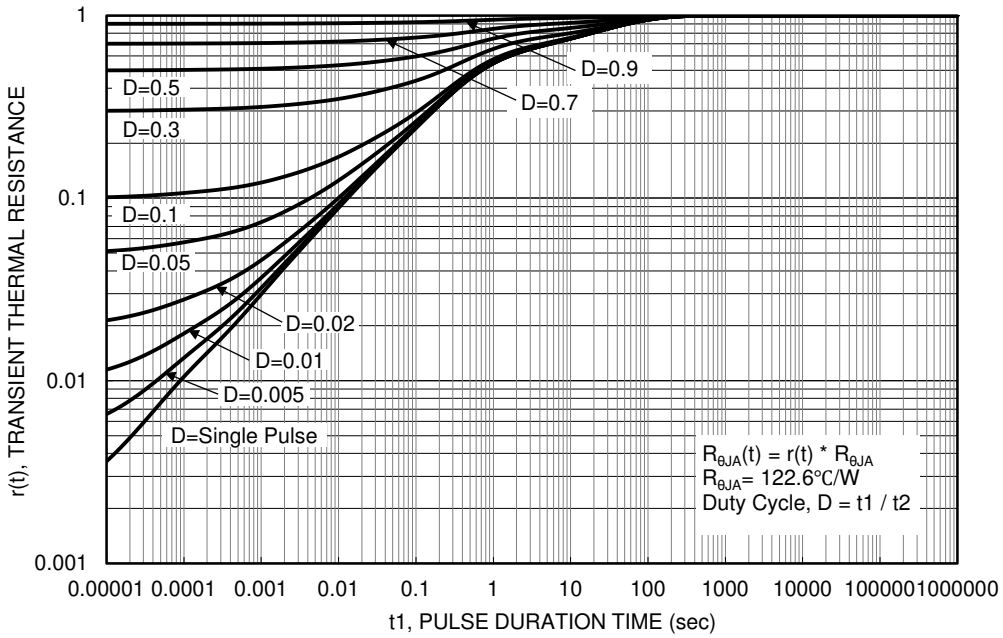

Figure 13. Transient Thermal Resistance

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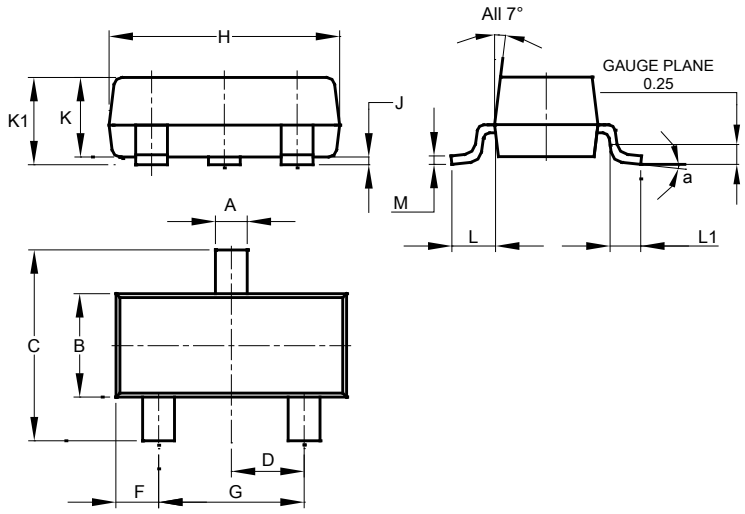
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

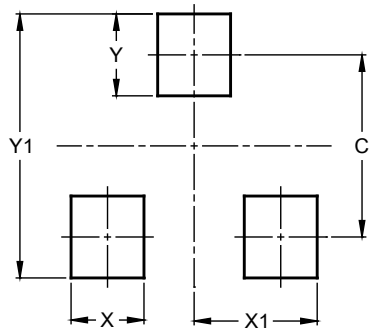


SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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